# **Operational Amplifier, Low Noise, Single**

The NE/SA/SE5534/5534A are single high-performance low noise operational amplifiers. Compared to other operational amplifiers, such as TL083, they show better noise performance, improved output drive capability, and considerably higher small-signal and power bandwidths.

This makes the devices especially suitable for application in high quality and professional audio equipment, in instrumentation and control circuits and telephone channel amplifiers. The op amps are internally compensated for gain equal to, or higher than, three. The frequency response can be optimized with an external compensation capacitor for various applications (unity gain amplifier, capacitive load, slew rate, low overshoot, etc.).

#### Features

- Small-Signal Bandwidth: 10 MHz
- Output Drive Capability: 600  $\Omega$ , 10 V<sub>RMS</sub> at V<sub>S</sub> = ± 18 V
- Input Noise Voltage:  $4 \text{ nV}/\sqrt{\text{Hz}}$
- DC Voltage Gain: 100000
- AC Voltage Gain: 6000 at 10 kHz
- Power Bandwidth: 200 kHz
- Slew Rate: 13 V/µs
- Large Supply Voltage Range:  $\pm 3.0$  to  $\pm 20$  V
- Pb-Free Packages are Available

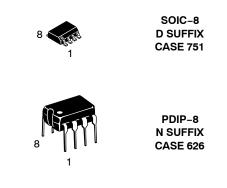
#### Applications

- Audio Equipment
- Instrumentation and Control Circuits
- Telephone Channel Amplifiers
- Medical Equipment

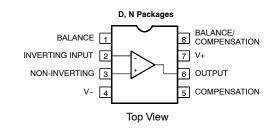


## **ON Semiconductor®**

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#### **PIN CONNECTIONS**



#### **DEVICE MARKING INFORMATION**

See general marking information in the device marking section on page 8 of this data sheet.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

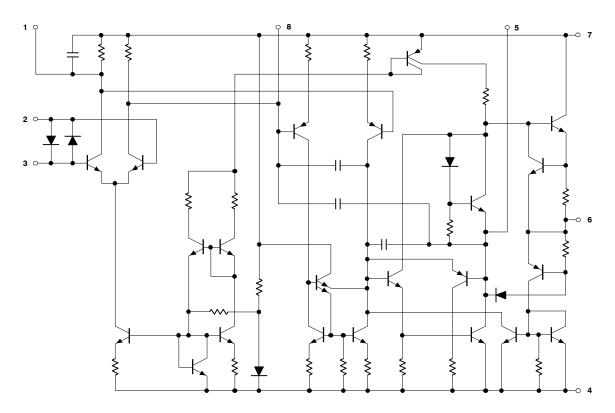


Figure 1. Equivalent Schematic

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Supply Voltage		V <sub>S</sub>	±22	V
Input Voltage		V <sub>IN</sub>	$\pm V$ Supply	V
Differential Input Voltage (Note 1)		V <sub>DIFF</sub>	±0.5	V
Operating Temperature Range NE SA SE		T <sub>amb</sub>	0 to +70 -40 to +85 -55 to +125	°C
Storage Temperature Range		T <sub>stg</sub>	-65 to +150	°C
Junction Temperature		Tj	150	°C
Power Dissipation at 25°C	N Package D Package	P <sub>D</sub>	1150 750	mW
Thermal Resistance, Junction-to-Ambient	N Package D Package	$R_{ ext{ heta}JA}$	130 158	°C/W
Output Short-Circuit Duration (Note 2)		_	Indefinite	-
Lead Soldering Temperature (10 sec max)		T <sub>sld</sub>	230	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Diodes protect the inputs against overvoltage. Therefore, unless current-limiting resistors are used, large currents will flow if the differential input

voltage exceeds 0.6 V. Maximum current should be limited to  $\pm 10$  mA. 2. Output may be shorted to ground at V<sub>S</sub> =  $\pm 15$  V, T<sub>amb</sub> = 25°C. Temperature and/or supply voltages must be limited to ensure dissipation rating is not exceeded.

			NE/SA5534/5534A			SE5534/5534A			
Characteristic	Symbol	Test Conditions	Min	Тур	Max	Min	Тур	Мах	Unit
	V <sub>OS</sub>		-	0.5	4.0	-	0.5	2.0	mV
Offset Voltage		Overtemperature	-	-	5.0	-	-	3.0	mV
	$\Delta V_{OS} / \Delta T$		-	5.0	-	-	5.0	_	μV/°C
	I <sub>OS</sub>		-	20	300	-	10	200	nA
Offset Current		Overtemperature	-	-	400	-	-	500	nA
	$\Delta I_{OS} / \Delta T$		-	200	-	-	200	-	pA/∘C
	Ι <sub>Β</sub>		-	500	1500	-	400	800	nA
Input Current		Overtemperature	-	-	2000	-	-	1500	nA
	$\Delta I_{B} / \Delta T$		-	5.0	-	-	5.0	_	nA/∘C
Supply Current Per Op Amp	Icc	Overtemperature		4.0 -	8.0 10		4.0 -	6.5 9.0	mA
Common Mode Input Range Common Mode Rejection Ratio Power Supply Rejection Ratio	V <sub>CM</sub> CMRR PSRR		±12 70 -	±13 100 10	- - 100	±12 80 -	±13 100 10	- - 50	V dB μV/V
Large-Signal Voltage Gain	A <sub>VOL</sub>	R <sub>L</sub> ≥600 Ω,	25	100	-	50	100	-	V/mV
		$V_{O}^{-} = \pm 10 V$ Overtemperature	15	-	-	25	-	-	
Output Swing	V <sub>OUT</sub>	$R_L \ge 600 \ \Omega$	±12	±13	-	±12	±13	-	V
		Overtemperature $R_L \ge 600 \Omega;$ $V_S = \pm 18 V$	±10 ±15	±12 ±16	-	±10 ±15	±12 16	-	
		$R_L \ge 2.0 \text{ k}\Omega$ Overtemperature	±13 ±12	±13.5 ±12.5	-	±13 ±12	± 13.5 ± 12.5	- -	
Input Resistance	R <sub>IN</sub>		30	100	-	50	100	_	kΩ
Output Short Circuit Current	I <sub>SC</sub>		-	38	-	-	38	_	mA

DC ELECTRICAL CHARACTERIST	<b>ICS</b> ( $T_{amb} = 25^{\circ}C$ ; $V_{S} = \pm 15$ V, unless otherwise noted.) (Notes 3, 4 and 5)
DO LLEOTNICAL CHANACTENIST	$U = 1$ ( $I_{amb} = 25$ C, $V_{S} = \pm 15$ V, unless of terwise noted.) (Notes 5, 4 and 5)

3. For NE5534/5534A,  $T_{MIN} = 0^{\circ}C$ ,  $T_{MAX} = 70^{\circ}C$ . 4. For SA5534/5534A,  $T_{MIN} = -40^{\circ}C$ ,  $T_{MAX} = +85^{\circ}C$ . 5. For SE5534/5534A,  $T_{MIN} = -55^{\circ}C$ ,  $T_{MAX} = +125^{\circ}C$ .

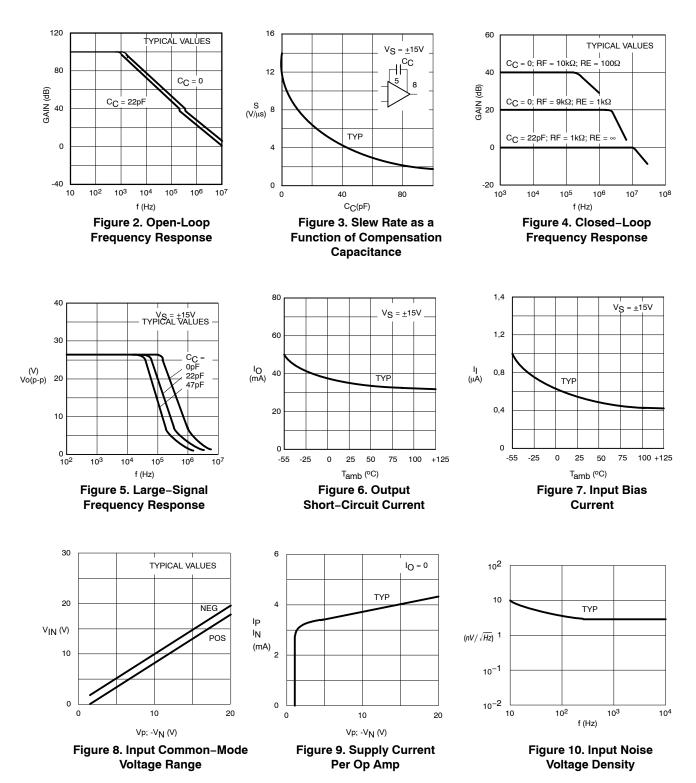
			NE/S	SA5534/55	534A	SI	E5534/553	4A	
Characteristic	Symbol	Test Conditions	Min	Тур	Max	Min	Тур	Max	Unit
Output Resistance	R <sub>OUT</sub>	$\begin{array}{l} A_V = 30 \text{ dB} \\ \text{closed-loop} \\ f = 10 \text{ kHz}; \\ B_L = 600 \ \Omega; \\ C_C = 22 \text{ pF} \end{array}$	_	0.3	_	_	0.3	_	Ω
Transient Response		$\label{eq:Voltage-follower,} \begin{array}{l} \mbox{Voltage-follower,} \\ \mbox{V}_{IN} = 50 \mbox{ mV} \\ \mbox{R}_L = 600 \ \Omega, \\ \mbox{C}_C = 22 \mbox{ pF}, \\ \mbox{C}_L = 100 \mbox{ pF} \end{array}$							
Rise Time	t <sub>R</sub>		-	20	-	-	20	-	ns
Overshoot	-		-	20	-	-	20	-	%
Transient Response		$V_{\rm IN} = 50 \text{ mV}, \\ R_{\rm L} = 600 \ \Omega, \\ C_{\rm C} = 47 \text{ pF}, \\ C_{\rm L} = 500 \text{ pF}$							
Rise Time	t <sub>R</sub>		-	50	-	-	50	-	ns
Overshoot	-		-	35	-	-	35	-	%
Gain	Av	$      f = 10 \text{ kHz}, C_C = 0 \\       f = 10 \text{ kHz}, \\       C_C = 22 \text{ pF} $	-	6.0 2.2			6.0 2.2		V/mV
Gain Bandwidth Product	GBW	C <sub>C</sub> = 22 pF, C <sub>L</sub> = 100 pF	-	10	-	-	10	-	MHz
Slew Rate	SR	C <sub>C</sub> = 0 C <sub>C</sub> = 22 pF	-	13 6.0	-	-	13 6.0		V/μs
Power Bandwidth	-	$\begin{array}{c} V_{OUT}=\pm10~V,\\ C_{C}=0~pF \end{array}$	-	200	-	-	200	-	kHz
		$V_{OUT} = \pm 10 \text{ V},$ $C_{C} = 22 \text{ pF}$	-	95	-	-	95	-	
		$V_{OUT} = \pm 14 \text{ V}, \\ R_{L} = 600 \Omega, \\ C_{C} = 22 \text{ pF}, \\ V_{CC} = \pm 18 \text{ V}$	-	70	_	-	70	_	

#### AC ELECTRICAL CHARACTERISTICS ( $T_{amb} = 25^{\circ}C$ ; $V_{S} = \pm 15$ V, unless otherwise noted.)

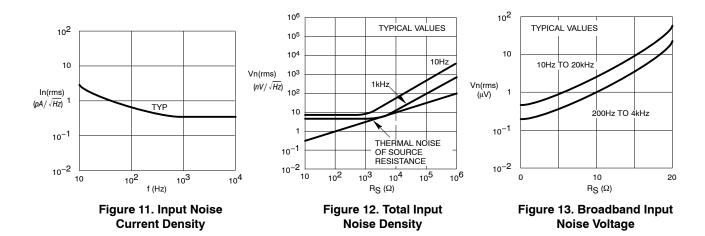
### **ELECTRICAL CHARACTERISTICS** (T<sub>amb</sub> = 25°C; V<sub>S</sub> = 15 V, unless otherwise noted.)

			NE/SA/SE5534		NE/SA/SE5534A				
Characteristic	Symbol	Test Conditions	Min	Тур	Max	Min	Тур	Max	Unit
Input Noise Voltage	V <sub>NOISE</sub>	f <sub>O</sub> = 30 Hz f <sub>O</sub> = 1.0 kHz		7.0 4.0		-	5.5 3.5	7.0 4.5	nV/√Hz
Input Noise Current	I <sub>NOISE</sub>	f <sub>O</sub> = 30 Hz f <sub>O</sub> = 1.0 kHz	-	2.5 0.6	-	-	1.5 0.4	-	pA/√Hz
Broadband Noise Figure	-	f = 10 Hz to 20 kHz; R <sub>S</sub> = 5.0 kΩ	-	-	-	-	0.9	-	dB
Channel Separation	-	f = 1.0 kHz; R <sub>S</sub> = 5.0 kΩ	-	110	-	-	110	-	dB

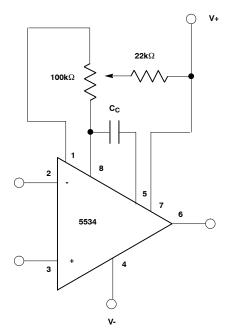
#### **TYPICAL PERFORMANCE CHARACTERISTICS**



### **TYPICAL PERFORMANCE CHARACTERISTICS**



#### **TEST LOAD CIRCUITS**



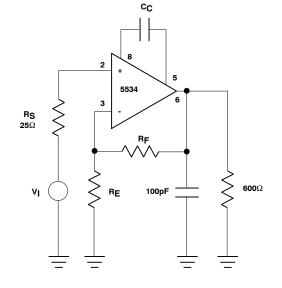


Figure 14. Frequency Compensation and Offset Voltage Adjustment Circuit

Figure 15. Closed-Loop Frequency Response

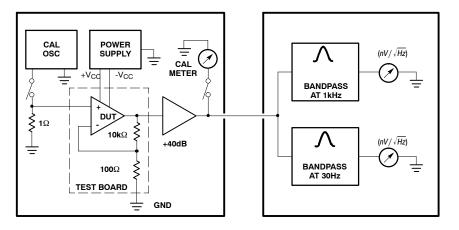
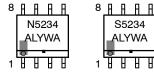


Figure 16. Noise Test Block Diagram

#### **MARKING DIAGRAMS**





8 8 8 8 8

S5234

ALYW

888

SOIC-8 D SUFFIX **CASE 751** 

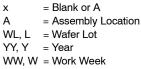






PDIP-8 **N SUFFIX** CASE 626





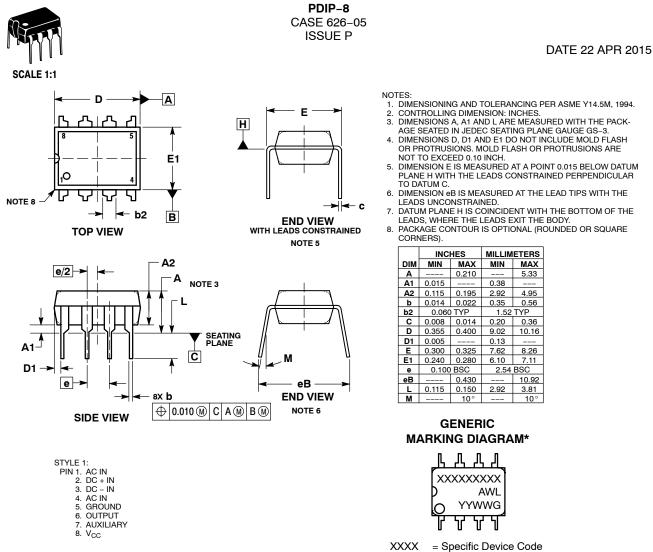
G or = Pb-Free Package

#### **ORDERING INFORMATION**

Device	Description	Temperature Range	Shipping <sup>†</sup>
NE5534AD	8-Pin Plastic Small Outline (SO-8) Package	0 to +70°C	98 Units / Rail
NE5534ADG	8-Pin Plastic Small Outline (SO-8) Package (Pb-Free)	0 to +70°C	98 Units / Rail
NE5534ADR2	8-Pin Plastic Small Outline (SO-8) Package	0 to +70°C	2500 / Tape & Reel
NE5534ADR2G	8-Pin Plastic Small Outline (SO-8) Package (Pb-Free)	0 to +70°C	2500 / Tape & Reel
NE5534AN	8-Pin Plastic Dual In-Line Package (PDIP-8)	0 to +70°C	50 Units / Rail
NE5534ANG	8-Pin Plastic Dual In-Line Package (PDIP-8) (Pb-Free)	0 to +70°C	50 Units / Rail
NE5534D	8-Pin Plastic Small Outline (SO-8) Package	0 to +70°C	98 Units / Rail
NE5534DG	8-Pin Plastic Small Outline (SO-8) Package (Pb-Free)	0 to +70°C	98 Units / Rail
NE5534DR2	8-Pin Plastic Small Outline (SO-8) Package	0 to +70°C	2500 / Tape & Reel
NE5534DR2G	8-Pin Plastic Small Outline (SO-8) Package (Pb-Free)	0 to +70°C	2500 / Tape & Reel
NE5534N	8-Pin Plastic Dual In-Line Package (PDIP-8)	0 to +70°C	50 Units / Rail
NE5534NG	8-Pin Plastic Dual In-Line Package (PDIP-8) (Pb-Free)	0 to +70°C	50 Units / Rail
SA5534AD	8-Pin Plastic Small Outline (SO-8) Package	–40 to +85°C	98 Units / Rail
SA5534ADG	8-Pin Plastic Small Outline (SO-8) Package (Pb-Free)	-40 to +85°C	98 Units / Rail
SA5534ADR2	8-Pin Plastic Small Outline (SO-8) Package	-40 to +85°C	2500 / Tape & Reel
SA5534ADR2G	8-Pin Plastic Small Outline (SO-8) Package (Pb-Free)	-40 to +85°C	2500 / Tape & Reel
SA5534AN	8-Pin Plastic Dual In-Line Package (PDIP-8)	-40 to +85°C	50 Units / Rail
SA5534ANG	8-Pin Plastic Dual In-Line Package (PDIP-8) (Pb-Free)	-40 to +85°C	50 Units / Rail
SA5534N	8-Pin Plastic Dual In-Line Package (PDIP-8)	-40 to +85°C	50 Units / Rail
SA5534NG	8-Pin Plastic Dual In-Line Package (PDIP-8) (Pb-Free)	-40 to +85°C	50 Units / Rail
SE5534AN	8-Pin Plastic Dual In-Line Package (PDIP-8)	–55 to +125°C	50 Units / Rail
SE5534ANG	8-Pin Plastic Dual In-Line Package (PDIP-8) (Pb-Free)	–55 to +125°C	50 Units / Rail
SE5534N	8-Pin Plastic Dual In-Line Package (PDIP-8)	–55 to +125°C	50 Units / Rail
SE5534NG	8-Pin Plastic Dual In-Line Package (PDIP-8) (Pb-Free)	–55 to +125°C	50 Units / Rail

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.





A = Assembly Location

- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present.



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\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### STYLES ON PAGE 2

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#### SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

6.

7.

8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 MIRROR 1 8. STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

#### DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 З. BASE #2 COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW\_TO\_GND 2. DASIC OFF DASIC\_SW\_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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7.

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COLLECTOR, #1

COLLECTOR, #1

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